

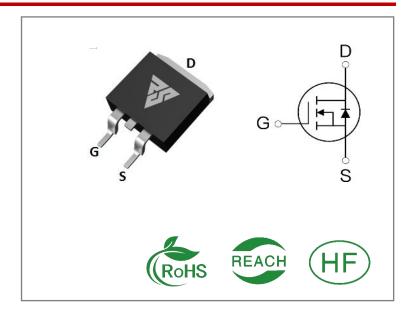
ID	R <sub>DS</sub> (ON)(Typ)	VDSS
16A	0.45Ω	650V

## **Applications:**

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

#### **Features:**

- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability



#### **Ordering Information**

Part Number	Package	Marking	Packing	Qty.
RS16N65S	T0-263	RS16N65S	Tape&reel	800 PCS

### Absolute Maximun Ratings Tc= 25°C unless otherwise specified

Symbol	Parameter	RS16N65S	Units
VDSS	Drain-to-Source Voltage	650	V
ID	Continuous Drain Current TC=25℃	16	۸
IDM	Pulsed Drain Current (Note*1)	64	А
PD	Power Dissipation	165	W
VGS	Gate- to- Source Voltage	±30	V
EAS	Single Pulse Avalanche Engergy L = 10mH,,VDD = 50V, RG = 25Ω	460	mJ
	Maximum Temperature for Soldering		
TL TPKG	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds	300 260	$^{\circ}$
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

<sup>\*</sup> Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" Table may cause permanent damage to the device.



#### **Thermal Resistance**

Symbol	Parameter	RS16N65S	Units	Test Conditions
RθJC	Junction-to-Case	0.75	°C/W	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 $^{\circ}\mathrm{C}$
RθJA	Junction-to- Ambient	62.5		1 cubic foot chamber,free air.

## **OFF Characteristics** TJ= 25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	650			V	VGS=0V,ID=250μ A
IDSS	Drain- to- Source Leakage Current			1	μΑ	VDS=650V,VGS= 0V
ICCC	Gate- to- Source Forward Leakage			100	- A	VGS=30V ,VDS=0 V
IGSS	Gate- to- Source Reverse Leakage			-100	nA	VGS=-30V ,VDS= 0V

# ON Characteristics TJ=25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On- Resistance(Note*2)		0.45	0.55	Ω	VGS=10V,ID=8A
VGS(TH	Gate Threshold Voltage	3		4	٧	VGS=VDS,ID=25 0μA

## Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time		55			
trise	Rise Time		40		C	VDS=325V
td(OFF)	Turn- OFF Delay Time		302		nS	ID=16A RG=25Ω
tfall	Fall Time		66			



**Dynamic Characteristics** Essentially independent of operating temperature

Symbol	Parameter	Min.	Тур.	Мах.	Units	Test Conditions
Ciss	Input Capacitance		2063			VGS=0V
Coss	Output Capacitance		204		рF	VDS=25V
Crss	Reverse Transfer Capacitance		29			f=1.0MHz
Qg	Total Gate Charge		74			VDS=520V
Qgs	Gate- to- Source Charge		10		nC	ID=16A
Qgd	Gate-to-Drain(" Miller") Charge		40			VGS=10V

#### **Source-Drain Diode Characteristics**

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
IS	Continuous Source Current			16	Α	Integral pn- diode
ISM	Maximum Pulsed Current			64	Α	in MOSFET
VSD	Diode Forward Voltage			1.4	V	IS=8A,VGS=0V
trr	Reverse Recovery Time		672		nS	VGS=0V
Qrr	Reverse Recovery Charge		4.5		μC	IS=16A,di/dt=100   Α/μs

#### Notes:

<sup>\* 1.</sup> Repetitive rating, pulse width limited by maximum junction temperature.

<sup>\* 2.</sup> Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%



## **Typical Feature Curve**

Figure 1. Output Characteristics (T<sub>J</sub> = 25°C)

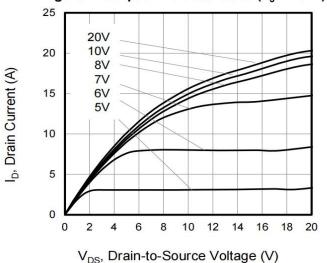


Figure 2. Body Diode Forward Voltage

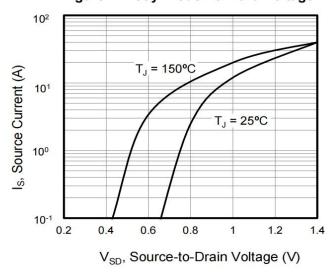


Figure 3. Drain Current vs. Temperature

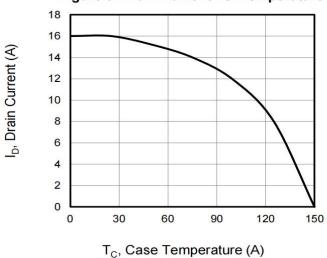


Figure 4. BV<sub>DSS</sub> Variation vs. Temperature

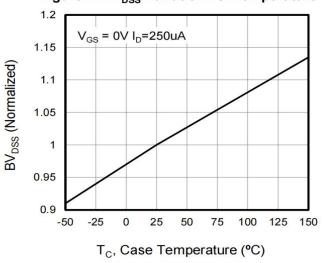
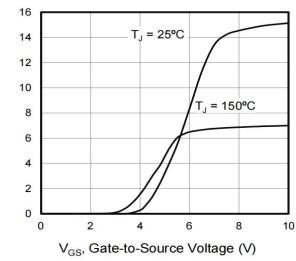
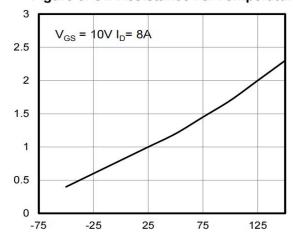


Figure 5. Transfer Characteristics



I<sub>D</sub>, Drain Current (A)

Figure 6. On-Resistance vs. Temperature



T<sub>J</sub>, Junction Temperature (°C)

R<sub>DS(on)</sub>, On-Resistance (Normalized)

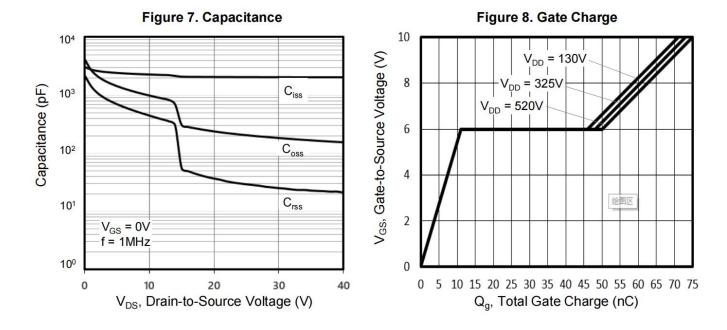
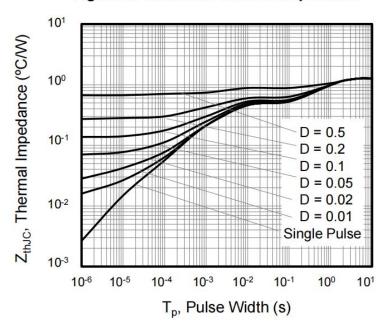


Figure 9. Transient Thermal Impedance





### **Test Circuits and Waveforms**

Figure A: Gate Charge Test Circuit and Waveform

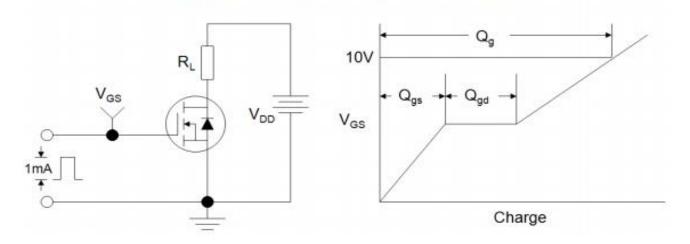


Figure B: Resistive Switching Test Circuit and Waveform

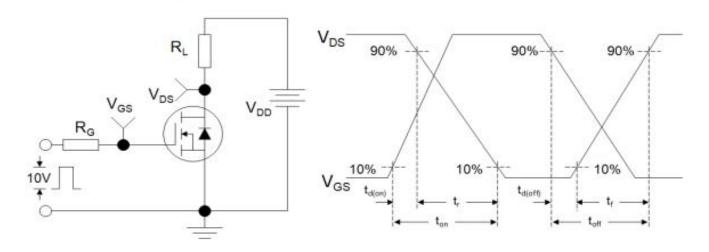
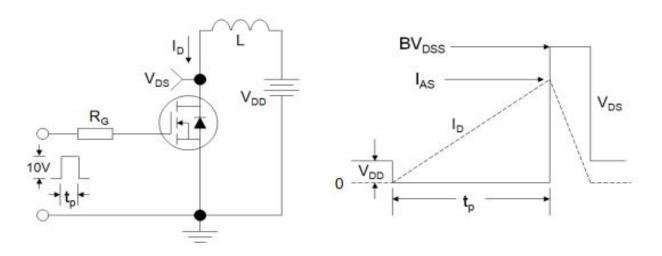
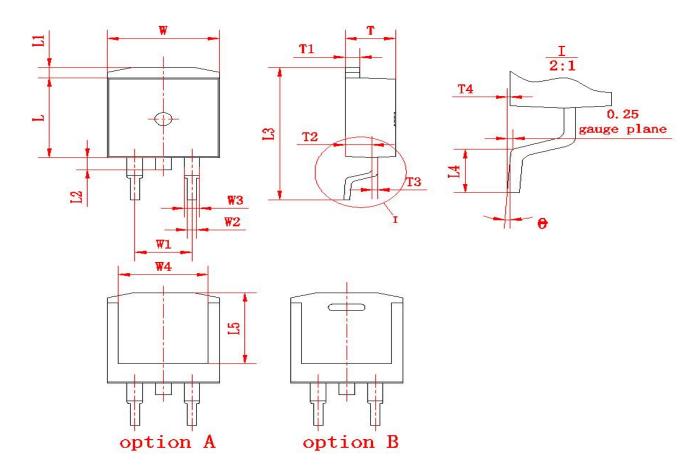


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





# Package outline drawing(TO-263 Unit: mm)



(单位: mm)

符号	尺寸		符号	尺	<b>寸</b>	75 D	尺寸	
गिर्	Min Max 195 Min Max	Max	符号	Min	Max			
W	9. 80	10. 20	L1	1.00	1.40	T1	1. 20	1. 40
W1	(5.	08)	L2	1. 20	1.60	T2	2. 20	2. 60
W2	0. 70	0. 95	L3	15. 00	15. 60	T3	0. 45	0. 65
W3	1. 17	1. 62	L4	2. 20	2. 80	T4	0	0. 25
<b>W</b> 4	(8)	. 0)	L5	(8. 2)		θ	0°	8°
L	9. 00	9. 40	T	4. 30	4. 70			



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DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B
IPB80P04P405ATMA2 2N7002W-G MCAC30N06Y-TP MCQ7328-TP NTMC083NP10M5L BXP7N65D BXP4N65F AOL1454G
WMJ80N60C4 BXP2N20L BXP2N65D BXT1150N10J BXT1700P06M TSM60NB380CP ROG RQ7L055BGTCR DMNH15H110SK3-13
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